

# CMOS Low Voltage 2.5 $\Omega$ Dual SPDT Switch

ADG736

#### **FEATURES**

1.8 V to 5.5 V Single Supply 2.5 Ω (Typ) On Resistance Low On Resistance Flatness –3 dB Bandwidth >200 MHz Rail-to-Rail Operation 10-Lead MSOP Package Fast Switching Times

t<sub>ON</sub> 16 ns t<sub>OFF</sub> 8 ns

Typical Power Consumption (<0.01 μW) TTL/CMOS Compatible

#### **APPLICATIONS**

USB 1.1 Signal Switching Circuits
Cell Phones
PDAs
Battery-Powered Systems
Communication Systems
Sample-and-Hold Systems
Audio Signal Routing
Audio and Video Switching
Mechanical Reed Relay Replacement

#### GENERAL DESCRIPTION

The ADG736 is a monolithic device comprised of two independently selectable CMOS SPDT switches. These switches are designed on a submicron process that provides low power dissipation yet gives high switching speed, low on resistance, low leakage currents, and wide input signal bandwidth.

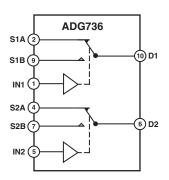
The on resistance profile is very flat over the full analog signal range. This ensures excellent linearity and low distortion when switching audio signals. Fast switching speed also makes the part suitable for video signal switching.

The ADG736 can operate from a single 1.8 V to 5.5 V supply, making it ideally suited to portable and battery-powered instruments

Each switch conducts equally well in both directions when on and each has an input signal range that extends to the power supplies. The ADG736 exhibits break-before-make switching action.

The ADG736 is available in a 10-lead MSOP package.

#### FUNCTIONAL BLOCK DIAGRAM



SWITCHES SHOWN FOR A LOGIC 1 INPUT

#### PRODUCT HIGHLIGHTS

- 1.8 V to 5.5 V Single-Supply Operation.
   The ADG736 offers high performance, including low on resistance and fast switching times and is fully specified and guaranteed with 3 V and 5 V supply rails.
- 2. Very Low  $R_{ON}$  (4.5  $\Omega$  Max at 5 V, 8  $\Omega$  Max at 3 V). At supply voltage of 1.8 V,  $R_{ON}$  is typically 35  $\Omega$  over the temperature range.
- 3. Low On Resistance Flatness.
- 4. −3 dB Bandwidth >200 MHz.
- Low Power Dissipation. CMOS construction ensures low power dissipation.
- 6. Fast  $t_{ON}/t_{OFF}$ .
- 7. Break-Before-Make Switching Action.
- 8. 10-Lead MSOP Package.

REV. A

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# $\label{eq:add-specifications} \textbf{ADG736-SPECIFICATIONS}^{1~(V_{DD}~=~5~V~\pm~10\%,~GND~=~0~V.~All~Specifications~-40°C~to~+85°C,~unless~otherwise~noted.)}$

	B Version -40°C to				
Parameter	25°C	+85°C	Unit	Test Conditions/Comments	
ANALOG SWITCH					
Analog Signal Range		$0~\mathrm{V}$ to $\mathrm{V}_{\mathrm{DD}}$	V		
On Resistance (R <sub>ON</sub> )	2.5	DD.	Ω typ	$V_{S} = 0 \text{ V to } V_{DD}, I_{DS} = -10 \text{ mA};$	
COLO	4	4.5	Ω max	Test Circuit 1	
On Resistance Match between	_				
Channels ( $\Delta R_{ON}$ )		0.1	Ω typ	$V_{S} = 0 \text{ V to } V_{DD}, I_{DS} = -10 \text{ mA}$	
		0.4	Ω max	, 2 , 10 , DD, DS	
On Resistance Flatness (R <sub>FLAT</sub> (ON))	0.5	0.1	$\Omega$ typ	$V_{S} = 0 \text{ V to } V_{DD}, I_{DS} = -10 \text{ mA}$	
On resistance 1 lattices (IGLA1 (ON))	0.5	1.2	$\Omega$ max	75 0 7 to 7 bb, 1bs 10 mm	
LEAKAGE CURRENTS				$V_{\rm DD} = 5.5  \rm V$	
Source OFF Leakage I <sub>S</sub> (OFF)	±0.01		nA typ	$V_{DD} = 3.5 \text{ V}$ $V_{S} = 4.5 \text{ V/1 V}, V_{D} = 1 \text{ V/4.5 V};$	
ordice of i Leakage is (OII)	±0.01 ±0.1	±0.3	nA max	Test Circuit 2	
Channel ON Leakage I <sub>D</sub> , I <sub>S</sub> (ON)	±0.01	±0.5	nA typ	$V_S = V_D = 1 \text{ V or } 4.5 \text{ V};$	
Chaimer ON Leakage 1D, 15 (ON)	±0.01 ±0.1	±0.3	nA typ	Test Circuit 3	
	±0.1	±0.5	III IIIax	Test Great 5	
DIGITAL INPUTS		2.4			
Input High Voltage, V <sub>INH</sub>		2.4	V min		
Input Low Voltage, V <sub>INL</sub>		0.8	V max		
Input Current					
I <sub>INL</sub> or I <sub>INH</sub>	0.005		μA typ	$V_{IN} = V_{INL}$ or $V_{INH}$	
		±0.1	μA max		
DYNAMIC CHARACTERISTICS <sup>2</sup>					
$t_{ON}$	12		ns typ	$R_L = 300 \Omega, C_L = 35 pF$	
		16	ns max	$V_S = 3 V$ ; Test Circuit 4	
$t_{ m OFF}$	5		ns typ	$R_L = 300 \Omega, C_L = 35 pF$	
		8	ns max	$V_S = 3 V$ ; Test Circuit 4	
Break-before-Make Time Delay, t <sub>D</sub>	7		ns typ	$R_{L} = 300 \Omega, C_{L} = 35 pF$	
,, _		1	ns min	$V_{S1} = V_{S2} = 3 \text{ V}$ ; Test Circuit 5	
Off Isolation	-62		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 10 MHz$	
	-82		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ;	
				Test Circuit 6	
Channel-to-Channel Crosstalk	-62		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 10 MHz$	
	-82		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ;	
				Test Circuit 7	
Bandwidth –3 dB	200		MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; Test Circuit 8	
$C_{S}(OFF)$	9		pF typ		
$C_D$ , $C_S$ (ON)	32		pF typ		
POWER REQUIREMENTS				V <sub>DD</sub> = 5.5 V	
2021.12.0112.112.112				Digital Inputs = 0 V or 5 V	
$I_{ m DD}$	0.001		μA typ	g 0 , 02 3 ,	
-עע	"""	1.0	uA max		

#### NOTES

Specifications subject to change without notice.

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 $<sup>^{1}</sup>Temperature$  range is  $-40^{\circ}C$  to +85°C for the B Version.

<sup>&</sup>lt;sup>2</sup>Guaranteed by design not subject to production test.

 $\label{eq:specifications} \textbf{SPECIFICATIONS}^{1} \ (\textbf{V}_{DD} = 3 \ \textbf{V} \ \pm \ 10\%, \ \textbf{GND} = 0 \ \textbf{V}. \ \textbf{All Specifications} \ -40^{\circ} \textbf{C} \ to \ +85^{\circ} \textbf{C}, \ unless \ otherwise \ noted.)$ 

	B Version -40°C to			
Parameter	25°C	+85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		0 V to V <sub>DD</sub>	V	
On Resistance (R <sub>ON</sub> )	5	5.5	$\Omega$ typ	$V_S = 0 \text{ V to } V_{DD}, I_{DS} = -10 \text{ mA};$
COLO		8	$\Omega$ max	Test Circuit 1
On Resistance Match between				
Channels ( $\Delta R_{ON}$ )	0.1		$\Omega$ typ	$V_S = 0 \text{ V to } V_{DD}, I_{DS} = -10 \text{ mA}$
OIV		0.4	$\Omega$ max	S S S S S S DD DO
On Resistance Flatness (R <sub>FLAT (ON)</sub> )		2.5	$\Omega$ typ	$V_S = 0 \text{ V to } V_{DD}, I_{DS} = -10 \text{ mA}$
LEAKAGE CURRENTS				$V_{\rm DD}$ = 3.3 V
Source OFF Leakage I <sub>S</sub> (OFF)	±0.01		nA typ	$V_S = 3 \text{ V/1 V}, V_D = 1 \text{ V/3 V};$
2 2 3 (2 2 )	±0.1	±0.3	nA max	Test Circuit 2
Channel ON Leakage ID, IS (ON)	±0.01	_ 0.0	nA typ	$V_S = V_D = 1 \text{ V or } 3 \text{ V};$
	±0.1	±0.3	nA max	Test Circuit 3
DIGITAL INPUTS				
Input High Voltage, V <sub>INH</sub>		2.0	V min	
Input Low Voltage, $V_{INL}$		0.4	V max	
Input Current		0.4	v IIIax	
I <sub>INL</sub> or I <sub>INH</sub>	0.005		μA typ	$V_{IN} = V_{INI}$ or $V_{INH}$
I <sub>INL</sub> of I <sub>INH</sub>	0.003	±0.1	μA max	VIN - VINL OF VINH
		±0.1	риз птах	
DYNAMIC CHARACTERISTICS <sup>2</sup>				D
$t_{ON}$	14		ns typ	$R_L = 300 \Omega, C_L = 35 pF$
		20	ns max	$V_S = 2 V$ ; Test Circuit 4
$t_{ m OFF}$	6		ns typ	$R_{L} = 300 \Omega, C_{L} = 35 pF$
	_	10	ns max	$V_S = 2 V$ ; Test Circuit 4
Break-before-Make Time Delay, t <sub>D</sub>	7	_	ns typ	$R_L = 300 \Omega, C_L = 35 pF$
0.007		1	ns min	$V_{S1} = V_{S2} = 2 \text{ V}$ ; Test Circuit 5
Off Isolation	-62		dB typ	$R_L = 50 \Omega, C_L = 5 pF, f = 10 MHz$
	-82		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ;
Channel-to-Channel Crosstalk	-62		dB typ	Test Circuit 6 $R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 10 MHz$
Chamber to Chamber Orostum	-82		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 10 MHz$ ;
	02		an typ	Test Circuit 7
Bandwidth –3 dB	200		MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; Test Circuit 8
$C_{S}$ (OFF)	9		pF typ	
$C_D$ , $C_S$ (ON)	32		pF typ	
POWER REQUIREMENTS				$V_{\rm DD} = 3.3 \text{ V}$
				Digital Inputs = 0 V or 3 V
$I_{\mathrm{DD}}$	0.001		μA typ	

Specifications subject to change without notice.

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NOTES  $^{1}$ Temperature range is  $-40^{\circ}$ C to  $+85^{\circ}$ C for the B Version.

<sup>&</sup>lt;sup>2</sup>Guaranteed by design not subject to production test.

#### **ADG736**

#### ABSOLUTE MAXIMUM RATINGS<sup>1</sup>

$(T_A = 25^{\circ}C, \text{ unless otherwise noted.})$
$V_{DD}$ to GND0.3 V to +6 V
Analog, Digital Inputs <sup>2</sup> 0.3 V to $V_{DD}$ + 0.3 V or
30 mA, Whichever Occurs First
Continuous Current, S or D
Peak Current, S or D
(Pulsed at 1 ms, 10% Duty Cycle Max)
Operating Temperature Range
Industrial (B Version)40°C to +85°C
Storage Temperature Range65°C to +150°C
Junction Temperature150°C
MSOP Package, Power Dissipation
$\theta_{JA}$ Thermal Impedance
Lead Temperature, Soldering (10 sec)300°C
IR Reflow, Peak Temperature (<20 sec)235°C
ESD

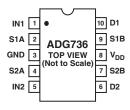
#### NOTES

#### **ORDERING GUIDE**

Model	Temperature Range	Branding	Package Option*
ADG736BRM	−40°C to +85°C	SAB	RM-10
ADG736BRM-REEL	−40°C to +85°C	SAB	RM-10
ADG736BRM-REEL7	−40°C to +85°C	SAB	RM-10

<sup>\*</sup>RM = MSOP

# PIN CONFIGURATION (10-Lead MSOP)



#### **TERMINOLOGY**

TERMINOLO	J1
$\overline{V_{\mathrm{DD}}}$	Most positive power supply potential.
GND	Ground (0 V) reference.
S	Source terminal. May be an input or output.
D	Drain terminal. May be an input or output.
IN	Logic control input.
$R_{ON}$	Ohmic resistance between D and S.
$\Delta R_{\rm ON}$	On resistance match between any two channels i.e., $R_{\rm ON}$ max – $R_{\rm ON}$ min.
$R_{\text{FLAT(ON)}}$	Flatness is defined as the difference between the maximum and minimum value of on resis- tance as measured over the specified analog signal range.
I <sub>S</sub> (OFF)	Source leakage current with the switch OFF.
$I_D$ , $I_S$ (ON)	Channel leakage current with the switch ON.
$V_{D}(V_{S})$	Analog voltage on terminals D and S.
$C_{S}$ (OFF)	OFF switch source capacitance.
$C_D$ , $C_S$ (ON)	ON switch capacitance.
$t_{ON}$	Delay between applying the digital control input and the output switching on. See Test Circuit 4.
t <sub>OFF</sub>	Delay between applying the digital control input and the output switching off.
$t_D$	OFF time or ON time measured between the 90% points of both switches, when switching from one address state to another. See Test Circuit 5.
Crosstalk	A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.
Off Isolation	A measure of unwanted signal coupling through an OFF switch.
Bandwidth	The frequency at which the output is attenuated by –3 dBs.
On Response	The frequency response of the ON switch.
On Loss	The voltage drop across the ON switch, seen on the on response versus frequency plot as how many dBs the signal is away from 0 dB at very low frequencies.

Table I. Truth Table

Logic	Switch A	Switch B	
0	Off	On	
1	On	Off	

#### **CAUTION**

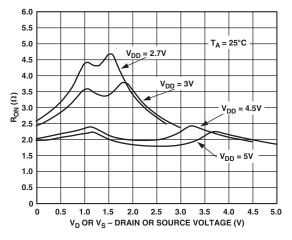
ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG736 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



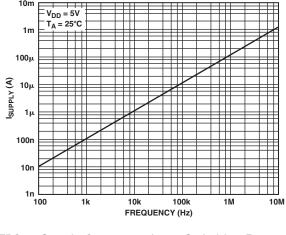
<sup>&</sup>lt;sup>1</sup>Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

<sup>&</sup>lt;sup>2</sup>Overvoltages at IN, S, or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

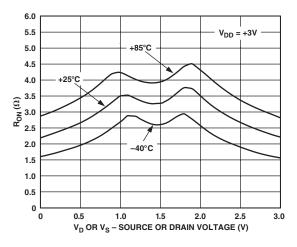
# **Typical Performance Characteristics—ADG736**



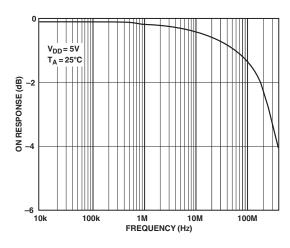
TPC 1. On Resistance as a Function of  $V_D$  ( $V_S$ ) Single Supplies



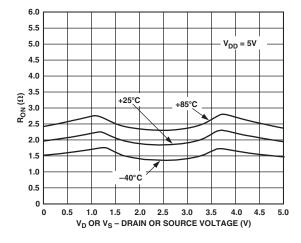
TPC 4. Supply Current vs. Input Switching Frequency



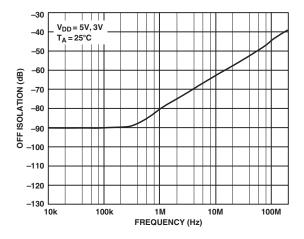
TPC 2. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures  $V_{DD} = 3 \ V$ 



TPC 5. On Response vs. Frequency



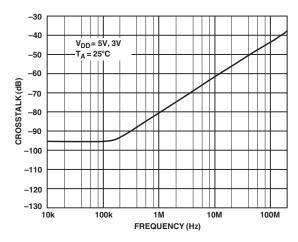
TPC 3. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures  $V_{DD} = 5 \ V$ 



TPC 6. Off Isolation vs. Frequency

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### **ADG736**



TPC 7. Crosstalk vs. Frequency

#### **APPLICATIONS**

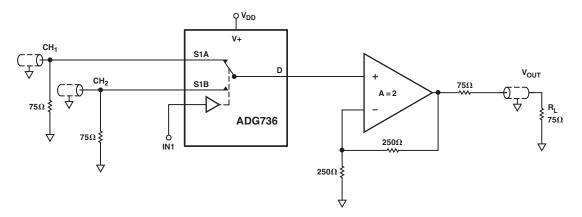
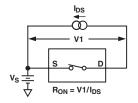
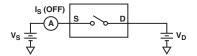


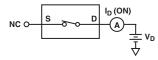
Figure 1. Using the ADG736 to Select between Two Video Signals

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# **Test Circuits**



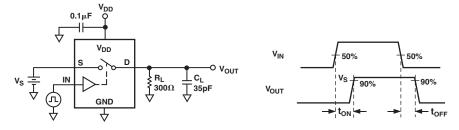




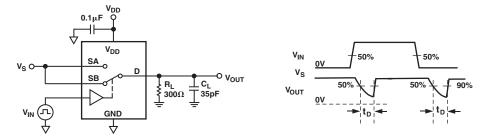
Test Circuit 1. On Resistance

Test Circuit 2. Off Leakage

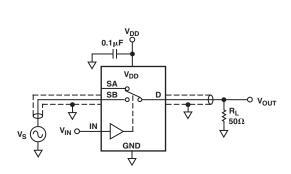
Test Circuit 3. On Leakage



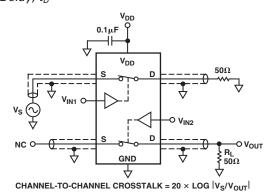
Test Circuit 4. Switching Times



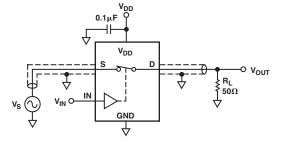
Test Circuit 5. Break-before-Make Time Delay, t<sub>D</sub>



Test Circuit 6. Off Isolation



Test Circuit 7. Channel-to-Channel Crosstalk



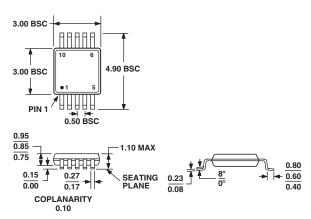
Test Circuit 8. Bandwidth

REV. A

#### **OUTLINE DIMENSIONS**

# 10-Lead Mini Small Outline Package [MSOP] (RM-10)

Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MO-187BA

# **Revision History**

Location	Page
11/03—Data Sheet changed from REV. 0 to REV. A.	
Renumbered Figures and TPCs	Universal
Change to title	1
Changes to APPLICATIONS	1
Changes to ABSOLUTE MAXIMUM RATINGS	4
Changes to ORDERING GUIDE	4
Changes to Test Circuit 3	7
Changes to OUTLINE DIMENSIONS	8